

Supporting information

Tailoring Molecular Size of Alkylamine Modifiers towards Efficient and Stable Inverted CsPbI₃ Perovskite Solar Cells

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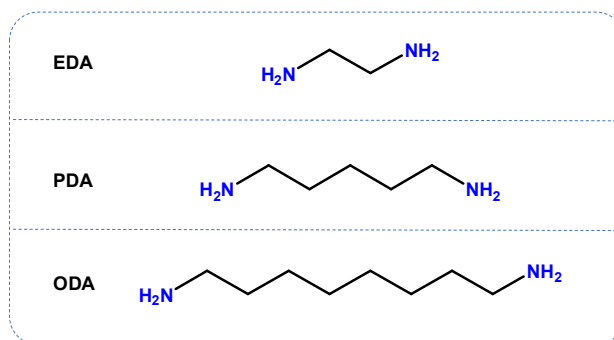


Fig. S1 The chemical structures of the three alkylamines (EDA, PDA, and ODA).

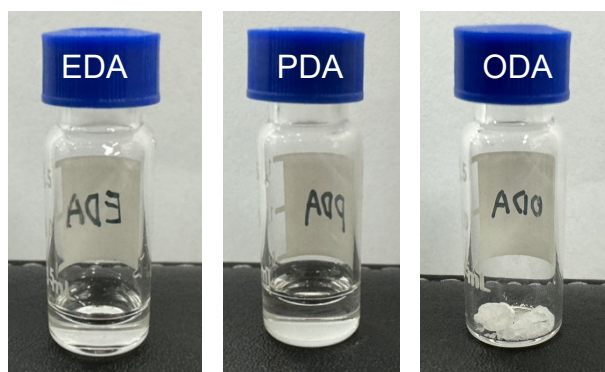


Fig. S2 The physical appearances of EDA, PDA, and ODA molecules under normal temperature and pressure.

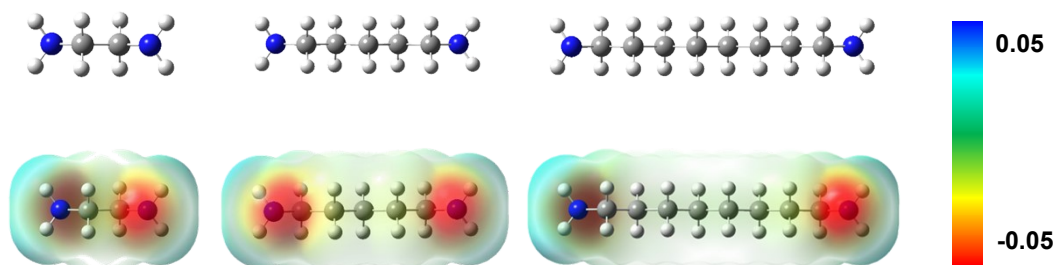


Fig. S3 The ESP analysis of EDA, PDA and ODA molecules.

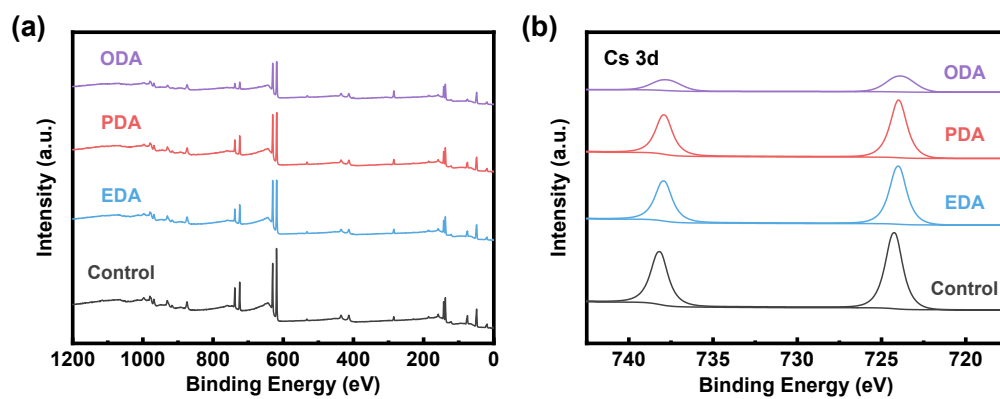


Fig. S4 (a) Full-scan XPS spectra of control, EDA, PDA, and ODA treated CsPbI₃ films. (b) XPS spectra of Cs 3d.

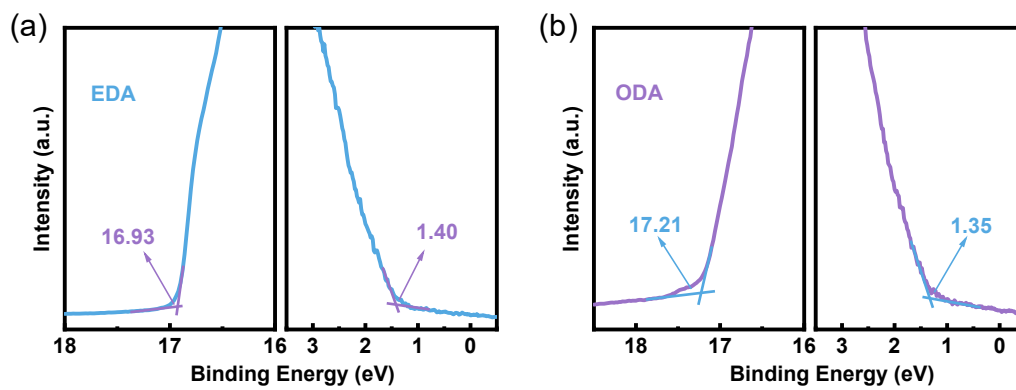


Fig. S5 UPS spectra of (a) EDA, and (b) ODA treated perovskite films.

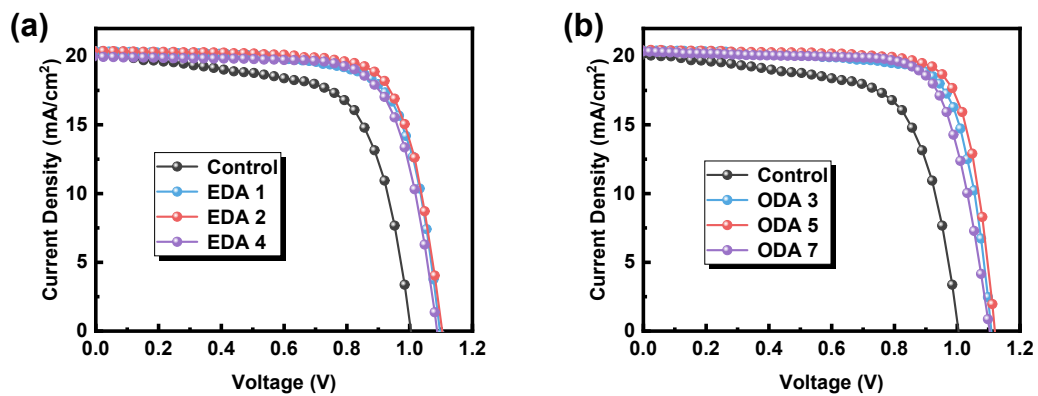


Fig. S6 J - V curve of devices treated with different concentration of (a) EDA, and (b) ODA.

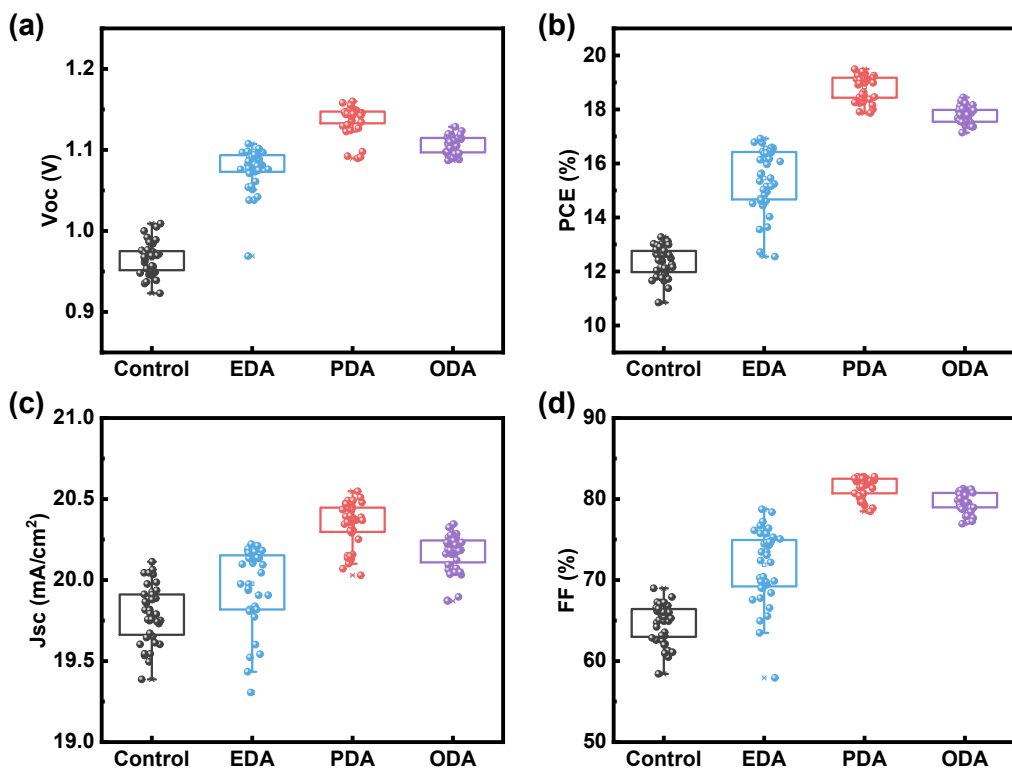


Fig. S7 Box data statistics charts of (a) V_{oc} , (b) PCE, (c) J_{sc} , and (d) FF.

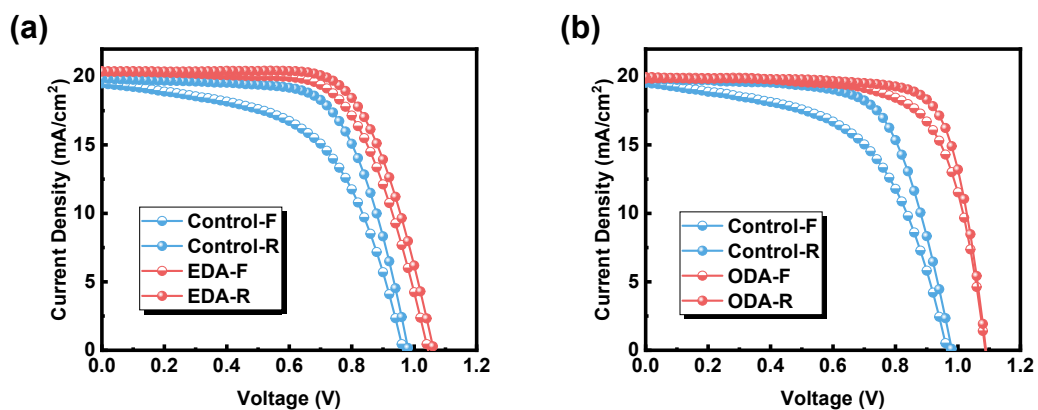


Fig. S8 J - V curves measured in forward and reverse scan directions of (a) EDA, and (b) ODA treated devices.

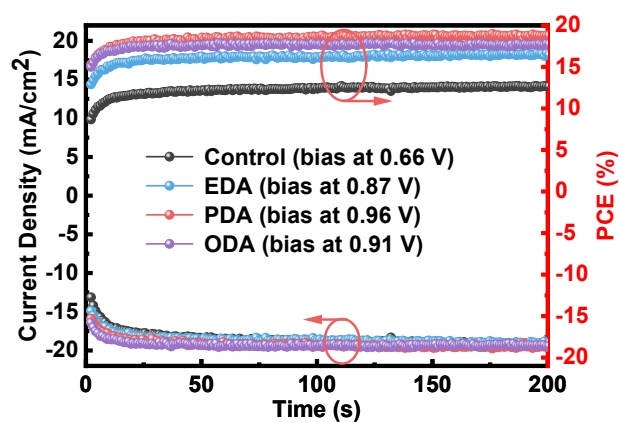


Fig. S9 Steady-state photocurrent and output PCE at the maximum power point of control, EDA, PDA, and ODA treated CsPbI₃ devices.

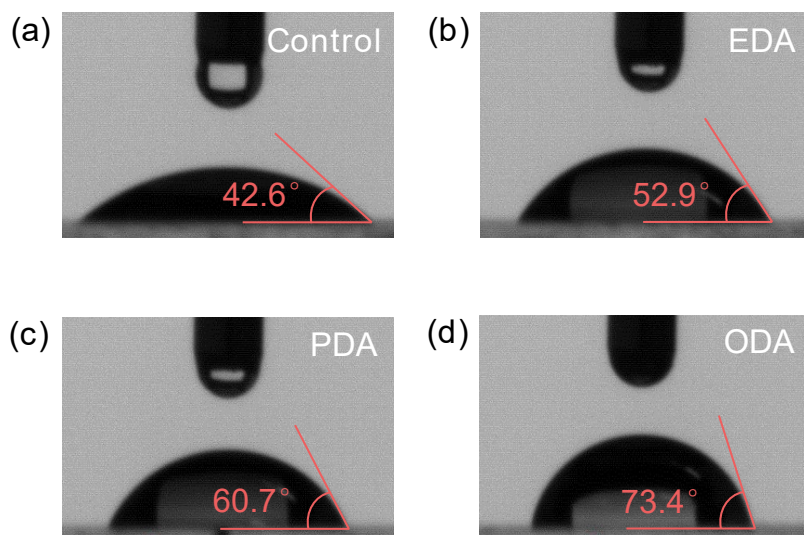


Fig. S10 The contact angle of water droplets on (a) control, (b) EDA, (c) PDA, and (d) ODA treated CsPbI₃ films, respectively.

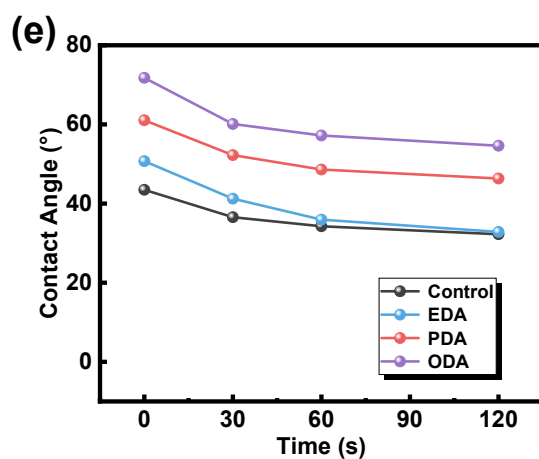
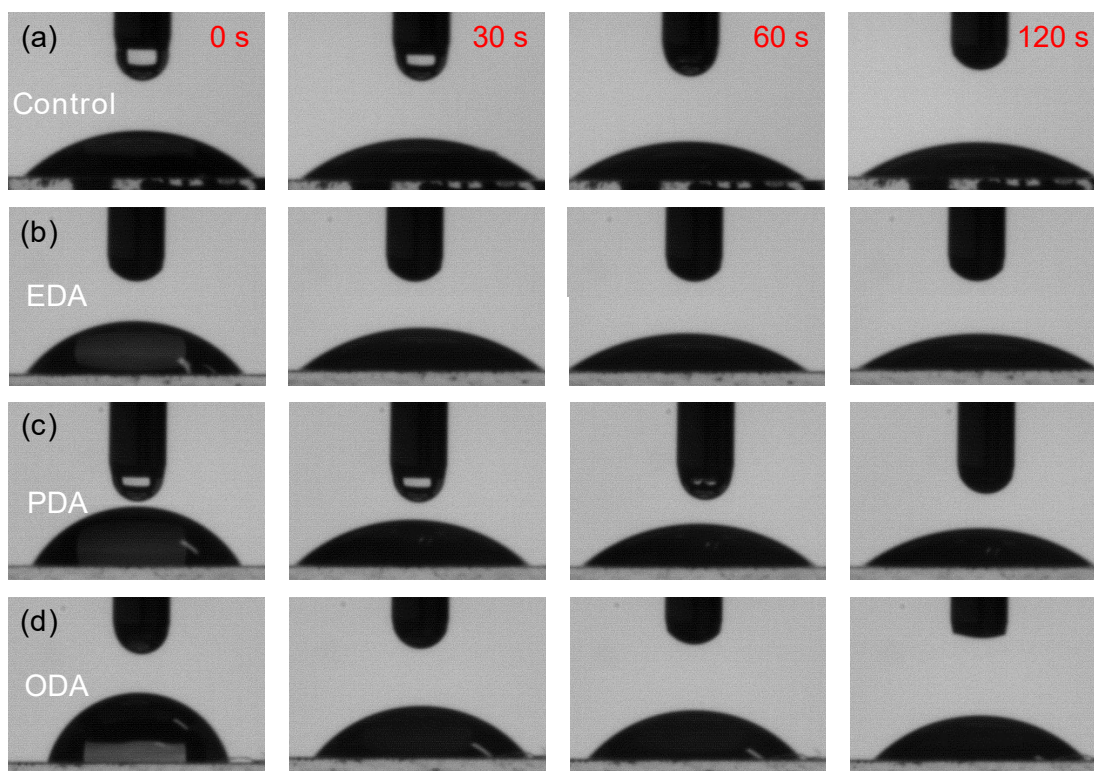


Fig. S11 Contact angle images of (a) control, (b) EDA, (c) PDA and (d) ODA treated films captured at different time, respectively; (e) Contact angle versus duration of exposure of four films.

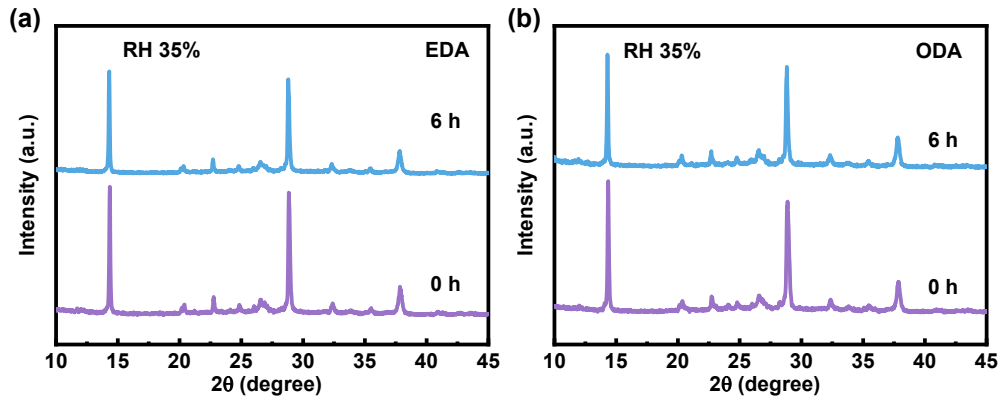


Fig. S12 The evolution of XRD patterns of (a) EDA, and (b) ODA treated CsPbI_3 films.

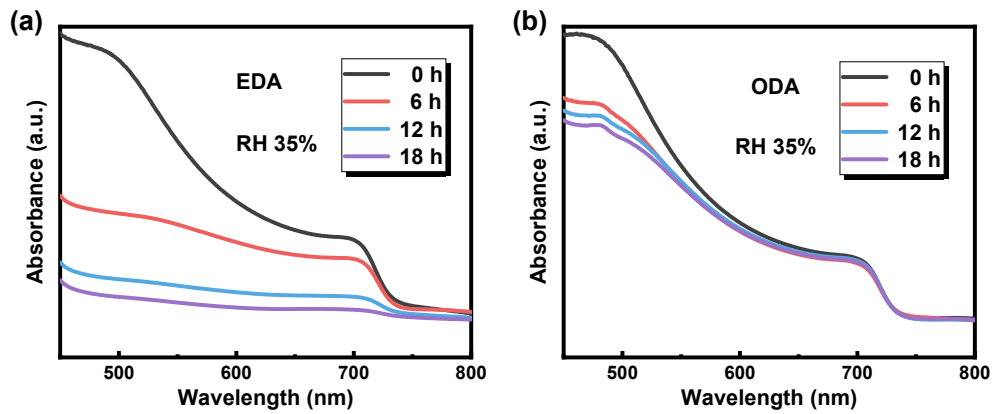


Fig. S13 UV-vis spectra of (a) EDA, and (b) ODA treated CsPbI_3 films.

Table S1 The basic physical properties of EDA, PDA, and ODA molecules.

Modifier	EDA	PDA	ODA
Formula	$C_2H_8N_2$	$C_5H_{14}N_2$	$C_8H_{20}N_2$
Physical appearance (25°C)	Liquid	Liquid	Solid
Molecular weight	60.1	102.2	144.2
Melting point (°C)	8.5	9	50
Boiling point (°C)	116	178	225
Vapor pressure (kPa)	1.21	0.13	<0.01

Table S2 Fitting parameters of the TRPL spectra of control, EDA, PDA, and ODA treated CsPbI₃ films.

Samples	A ₁	τ_1 /ns	A ₂	τ_2 /ns	τ_{avg} /ns
Control	2.32	11.79	88.23	5.37	5.72
EDA	2.16	10.01	1.79	24.71	19.88
PDA	1.06	19.05	1.06	52.26	43.39
ODA	11.23	6.64	0.90	45.22	20.26

Table S3 The band structure parameters of control, EDA, PDA, and ODA treated CsPbI₃ films, respectively.

Samples	E_{cutoff} (eV)	E_{onset} (eV)	VB (eV)	CB (eV)	E_F (eV)
Control	16.84	1.30	5.68	4.00	4.38
EDA	16.93	1.40	5.69	4.01	4.29
PDA	16.99	1.56	5.79	4.11	4.23
ODA	17.21	1.35	5.36	3.68	4.01

Table S4 The photovoltaic parameters of devices based on different concentrations of EDA, PDA, and ODA solutions treatment.

Sample (mg/mL)	V_{oc} (V)	J_{sc} (mA/cm ²)	FF (%)	PCE (%)
Control	0.997	20.04	67.24	13.43
EDA 1	1.096	20.24	73.32	16.26
EDA 2	1.105	20.18	75.28	16.79
EDA 4	1.077	20.12	72.41	15.69
PDA 4	1.117	20.35	82.95	18.85
PDA 6	1.151	20.39	83.18	19.52
PDA 8	1.105	20.27	82.31	18.43
ODA 3	1.108	20.24	80.45	18.04
ODA 5	1.116	20.26	81.34	18.39
ODA 7	1.101	20.21	77.38	17.22

Table S5 The photovoltaic parameters of the control, EDA, PDA, and ODA treated CsPbI₃ PSCs.

Sample	V_{OC} (V)	J_{SC} (mA/cm ²)	FF (%)	PCE (%)
Control	0.997 (0.966±0.0194)	20.04 (19.79±0.18)	67.24 (64.77±2.59)	13.43 (12.37±0.55)
EDA	1.105 (1.077±0.025)	20.18 (19.98±0.24)	75.28 (71.87±4.43)	16.79 (15.46±1.14)
PDA	1.151 (1.137±0.017)	20.39 (20.34±0.13)	83.18 (81.57±1.24)	19.52 (18.86±0.46)
ODA	1.116 (1.106±0.010)	20.26 (20.17±0.11)	81.34 (79.67±1.18)	18.39 (17.78±0.30)